

Silicon NPN Power Transistors

2SC4928

DESCRIPTION

- With TO-3PL package
- High speed switching
- High breakdown voltage,high current

APPLICATIONS

- Character display horizontal deflection output applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

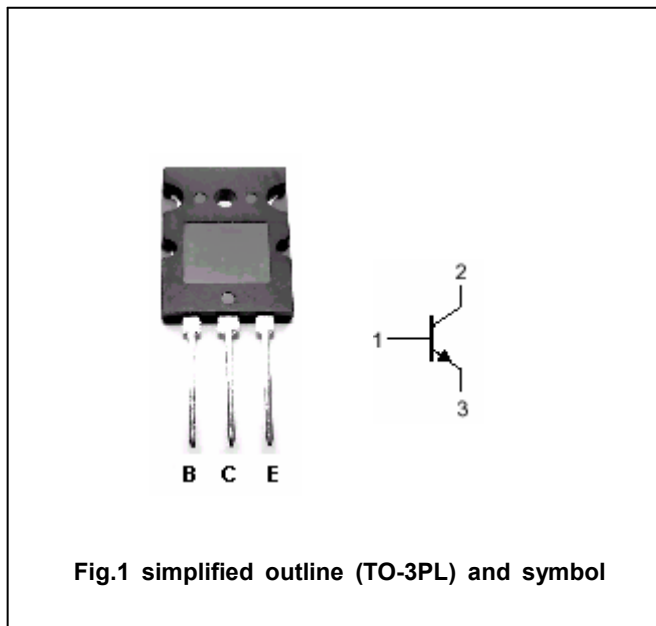


Fig.1 simplified outline (TO-3PL) and symbol

Absolute maximum ratings(Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	1500	V
V _{CEO}	Collector-emitter voltage	Open base	800	V
V _{EBO}	Emitter-base voltage	Open collector	6	V
I _C	Collector current		15	A
I _{C(surge)}	Collector surge current		20	A
P _C	Collector power dissipation	T _C =25°C	150	W
T _j	Junction temperature		150	°C
T _{stg}	Storage temperature		-55~150	°C

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CHARACTERISTICS

T_j=25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =10mA; R _{BE} =∞	800			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =10mA; I _C =0	6			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =12A; I _B =3A			5.0	V
V _{BEsat}	Base-emitter saturation voltage	I _C =12A; I _B =3A			1.5	V
I _{CES}	Collector cut-off current	V _{CB} =1500V; R _{BE} =0			500	μA
I _{EBO}	Emitter cut-off current	V _{EB} =6V; I _C =0			500	μA
h _{FE}	DC current gain	I _C =1A; V _{CE} =5V			38	
t _f	Fall time	I _C =8A; I _{B1} =1.4A; I _{B2} ≈-2.5A f _H =31.5kHz			0.5	μs

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PACKAGE OUTLINE

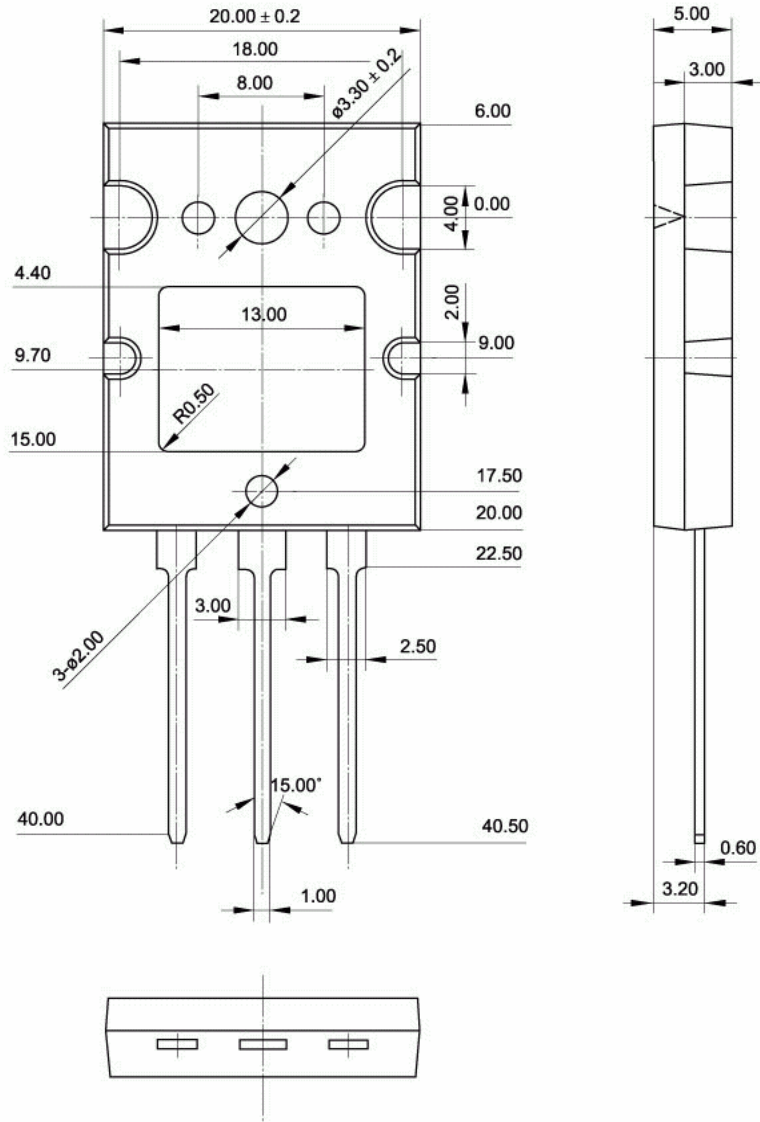


Fig.2 Outline dimensions (unindicated tolerance: ± 0.50 mm)